

ABSTRACT

The present invention is an apparatus and method for eliminating parasitic bipolar transistor action in a Silicon on Insulator (SOI) Metal Oxide Semiconductor (MOS) device.

- 5 In accordance with the invention a SOI electronic device and an active discharging device coupled to said SOI electronic device is provided to deactivate the parasitic bipolar transistor. The parasitic bipolar transistor action is deactivated by controlling the conduction of an active
10 discharging device, said active discharging device being coupled to said SOI device.

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